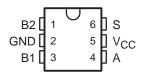
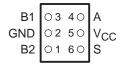
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- 1.65-V to 5.5-V V<sub>CC</sub> Operation
- **Useful for Both Analog and Digital Applications**
- Specified Break-Before-Make Switching
- Rail-to-Rail Signal Handling
- **High Degree of Linearity**
- High Speed, Typically 0.5 ns  $(V_{CC} = 3 V, C_{L} = 50 pF)$
- Low On-State Resistance, Typically  $\approx$ 6  $\Omega$  $(V_{CC} = 4.5 V)$
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

#### **DBV OR DCK PACKAGE** (TOP VIEW)



#### YEP OR YZP PACKAGE (BOTTOM VIEW)



#### description/ordering information

This single-pole, double-throw (SPDT) analog switch is designed for 1.65-V to 5.5-V V<sub>CC</sub> operation.

The SN74LVC1G3157 can handle both analog and digital signals. The device permits signals with amplitudes of up to V<sub>CC</sub> (peak) to be transmitted in either direction.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

#### ORDERING INFORMATION

TA	PACKAGE <sup>†</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING‡		
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Tone and real	SN74LVC1G3157YEPR	C5	
-40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	SN74LVC1G3157YZPR	05_	
	SOT (SOT-23) – DBV	Tape and reel	SN74LVC1G3157DBVR	CC5_	
	SOT (SC-70) – DCK	Tape and reel	SN74LVC1G3157DCKR	C5_	

<sup>†</sup>Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

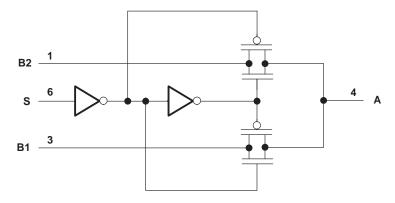


DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site. YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition  $(1 = SnPb, \bullet = Pb-free).$ 

#### **FUNCTION TABLE**

CONTROL INPUT S	ON CHANNEL	
L	B1	
Н	B2	

#### logic diagram (positive logic)



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub> (see Note 1)	–0.5 V to 6.5 V
Control input voltage range, V <sub>IN</sub> (see Notes 1 and 2)	–0.5 V to 6.5 V
Switch I/O voltage range, V <sub>I/O</sub> (see Notes 1, 2, 3, and 4)	$\dots$ -0.5 V to V <sub>CC</sub> + 0.5 V
Control input clamp current, I <sub>IK</sub> (V <sub>IN</sub> < 0)	–50 mA
I/O port diode current, $I_{IOK}$ ( $V_{I/O}$ < 0 or $V_{I/O} > V_{CC}$ )	±50 mA
On-state switch current, $I_{I/O}$ ( $V_{I/O} = 0$ to $V_{CC}$ ) (see Note 5)	±128 mA
Continuous current through V <sub>CC</sub> or GND	±100 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 6): DBV package	165°C/W
DCK package	259°C/W
YEP/YZP package	123°C/W
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to ground unless otherwise specified.
  - 2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
  - 3. This value is limited to 5.5 V maximum.
  - 4.  $V_I$ ,  $V_O$ ,  $V_A$ , and  $V_{Bn}$  are used to denote specific conditions for  $V_{I/O}$ .
  - 5.  $I_I$ ,  $I_O$ ,  $I_A$ , and  $I_{Bn}$  are used to denote specific conditions for  $I_{I/O}$ .
  - 6. The package thermal impedance is calculated in accordance with JESD 51-7.



# SN74LVC1G3157 SINGLE-POLE, DOUBLE-THROW ANALOG SWITCH

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# recommended operating conditions (see Note 7)

			MIN	MAX	UNIT	
Vcc			1.65	5.5	V	
V <sub>I/O</sub>			0	Vcc	V	
VIN			0	5.5	V	
\/	High-level input voltage, control input	V <sub>CC</sub> = 1.65 V to 1.95 V	V <sub>CC</sub> × 0.75		V	
VIH	nigh-level input voltage, control input	V <sub>CC</sub> = 2.3 V to 5.5 V	V <sub>CC</sub> ×0.7		V	
\/	Low-level input voltage, control input	V <sub>CC</sub> = 1.65 V to 1.95 V	V <sub>CC</sub> ×0.2		V	
VIL	Low-level input voitage, control input	V <sub>CC</sub> = 2.3 V to 5.5 V		V <sub>CC</sub> ×0.3	V	
		V <sub>CC</sub> = 1.65 V to 1.95 V		20		
Δt/Δν	Input transition rise fall time	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		20	ns/V	
ΔυΔν	Input transition rise/fall time	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		10		
		V <sub>CC</sub> = 4.5 V to 5.5 V		10		
TA			-40	85	°C	

NOTE 7: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER			TEST CONDITIONS			VCC	MIN TYP1	MAX	UNIT	
				V <sub>I</sub> = 0 V	I <sub>O</sub> = 4 mA		11	20		
			V <sub>I</sub> = 1.65 V	$I_O = -4 \text{ mA}$	1.65 V	15	50	1		
				V <sub>I</sub> = 0 V	IO = 8 mA	221/	8	12	1	
			_	V <sub>I</sub> = 2.3 V	$I_O = -8 \text{ mA}$	2.3 V	11	30	1	
ron	On-state switch resistance	ce‡	See Figures 1 and 2	V <sub>I</sub> = 0 V	I <sub>O</sub> = 24 mA	3 V	7	9	Ω	
			riguics rand 2	V <sub>I</sub> = 3 V	$I_{O} = -24 \text{ mA}$	3 V	9	20	]	
				V <sub>I</sub> = 0 V	$I_O = 30 \text{ mA}$		6	7		
				V <sub>I</sub> = 2.4 V	$I_{O} = -30 \text{ mA}$	4.5 V	7	12	]	
				V <sub>I</sub> = 4.5 V	$I_{O} = -30 \text{ mA}$		7	15		
					$I_A = -4 \text{ mA}$	1.65 V		140		
	On-state switch resistand	се	$0 \le V_{Bn} \le V_{CC}$		$I_A = -8 \text{ mA}$	2.3 V		45	$\Omega$	
<sup>r</sup> range	over signal range‡§		(see Figures 1 a	nd 2)	$I_A = -24 \text{ mA}$	3 V		18	1 12	
					$I_A = -30 \text{ mA}$	4.5 V		10		
				V <sub>Bn</sub> = 1.15 V	$I_A = -4 \text{ mA}$	1.65 V	0.5			
۸.	Difference of on-state		See Figure 1	V <sub>Bn</sub> = 1.6V	$I_A = -8 \text{ mA}$	2.3 V	0.1			
$\Delta r_{ m on}$	resistance between switches‡¶#		See Figure 1	V <sub>Bn</sub> = 2.1 V	$I_A = -24 \text{ mA}$	3 V	0.1		Ω	
				$V_{Bn} = 3.15 \text{ V}$	$I_A = -30 \text{ mA}$	4.5 V	0.1			
					$I_A = -4 \text{ mA}$	1.65 V	110			
r (11 )	ON resistance flatness‡¶	TII	1 <sub>A</sub> = -{		$I_A = -8 \text{ mA}$	2.3 V	26		Ω	
<sup>r</sup> on(flat)	ON resistance natness+	'''			$I_A = -24 \text{ mA}$	3 V	g		1 22	
					$I_A = -30 \text{ mA}$	4.5 V	4			
	Off-state switch leakage	ourront	0 ≤ V <sub>I</sub> , V <sub>O</sub> ≤ V <sub>CO</sub>	(acc Figure 2)		1.65 V		±1		
l <sub>off</sub> ☆	Oil-state switch leakage	current	$0 \ge \Lambda^{1}, \Lambda Q \ge \Lambda CC$	;, (see Figure 3)		to 5.5 V	±0.05	±1†	μΑ	
lar v	On atota quitab lackage		VI = VCC or GND	),		5.5 V		±1		
IS(on)	On-state switch leakage	current	V <sub>O</sub> = Open (see	Figure 4)		5.5 V		±0.1 <sup>†</sup>	μΑ	
lu.	Control input ourrent		0<\/>\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\			0 V to		±1		
IN	Control input current		$0 \le AIN \le ACC$			5.5 V	±0.05	±1†	μΑ	
Icc	Supply current		V <sub>IN</sub> = V <sub>CC</sub> or GND			5.5 V	1	10	μА	
Δlcc	Supply-current change		V <sub>IN</sub> = V <sub>CC</sub> - 0.6 V			5.5 V		500	μΑ	
C <sub>in</sub>	Control input capacitance	s				5 V	2.7		pF	
C <sub>io(off)</sub>	Switch input/output capacitance	Bn				5 V	5.2		pF	
C <sub>io(on)</sub>	Switch input/output capacitance	Bn A				5 V	17.3 17.3		pF	



<sup>‡</sup> Measured by the voltage drop between I/O pins at the indicated current through the switch. ON resistance is determined by the lower of the voltages on the two (A or B) ports.

<sup>§</sup> Specified by design

 $<sup>\</sup>P$   $\Delta r_{OD} = r_{OD}(max) - r_{OD}(min)$  measured at identical  $V_{CC}$ , temperature, and voltage levels. # This parameter is characterized, but not tested in production.

Flatness is defined as the difference between the maximum and minimum values of ON resistance over the specified range of conditions.

 $<sup>^{\</sup>star}$ I<sub>off</sub> is the same as I<sub>S(off)</sub> (off-state switch leakage current).

# analog switch characteristics, T<sub>A</sub> = 25°C

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	vcc	TYP	UNIT
				1.65 V	300	
Frequency response	A or Do	Bn or A	$R_L = 50 \Omega$ ,	2.3 V	300	NAL 1-
(switch on)†	A or Bn	DIT OF A	f <sub>in</sub> = sine wave (see Figure 6)	3 V	300	MHz
			( · · · · · · · · · · · · · · · · · · ·	4.5 V	300	
				1.65 V	-54	
Crosstalk	B1 or B2	B2 or B1	$R_L = 50 \Omega$ ,	2.3 V	-54	dB
(between switches)‡	B1 01 B2	D2 01 D1	f <sub>in</sub> = 10 MHz (sine wave) (see Figure 7)	3 V	-54	
			(g	4.5 V	-54	
	A or Bn	Bn or A		1.65 V	<b>–</b> 57	dB
Feed-through attenuation			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	<b>–</b> 57	
(switch off)‡			f <sub>in</sub> = 10 MHz (sine wave) (see Figure 8)	3 V	<b>–</b> 57	
			(*** 9* * *)	4.5 V	-57	
8	S	А	$C_{I} = 0.1 \text{ nF, } R_{I} = 1 \text{ M}\Omega,$	3.3 V	3	~C
Charge injection§	5	A	(see Figure 9)	5 V	7	pC
			$V_{\parallel} = 0.5 \text{ V p-p, R}_{\parallel} = 600 \Omega,$	1.65 V	0.1	%
Total harmonic distortion	A or Do	Do or A	$f_{in} = 600 \text{ Hz to } 20 \text{ kHz}$	2.3 V	0.025	
	A or Bn	Bn or A	(sine wave)	3 V	0.015	
			(see Figure 10)	4.5 V	0.01	

<sup>†</sup> Adjust fin voltage to obtain 0 dBm at output. Increase fin frequency until dB meter reads –3 dB.

# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 5 and 11)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = ± 0.1		V <sub>CC</sub> =		V <sub>CC</sub> =		VCC =		UNIT
	(INFOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$t_{pd}\P$	A or Bn	Bn or A		2		1.2		0.8		0.3	ns
t <sub>en</sub> #	s	Bn	7	24	3.5	14	2.5	7.6	1.7	5.7	no
t <sub>dis</sub>	3	ы	3	13	2	7.5	1.5	5.3	0.8	3.8	ns
t <sub>B-M</sub> ☆			0.5		0.5		0.5		0.5		ns

<sup>¶</sup> tpd is the slower of tpLH or tpHL. The propagation delay is calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance when driven by an ideal voltage source (zero output impedance).



<sup>‡</sup> Adjust fin voltage to obtain 0 dBm at input.

<sup>§</sup> Specified by design

 $<sup>\</sup>ensuremath{^{\#}}\xspace t_{en}$  is the slower of tpZL or tpZH.

Itdis is the slower of tpLZ or tpHZ.

<sup>\*</sup>Specified by design

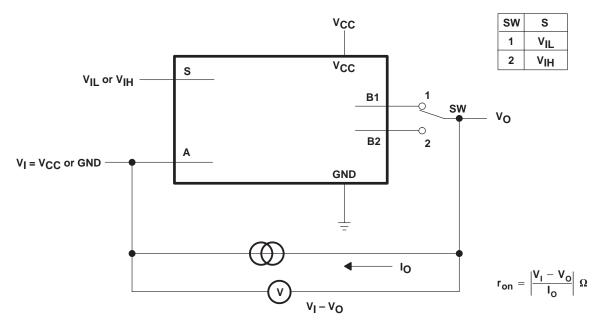


Figure 1. On-State Resistance Test Circuit

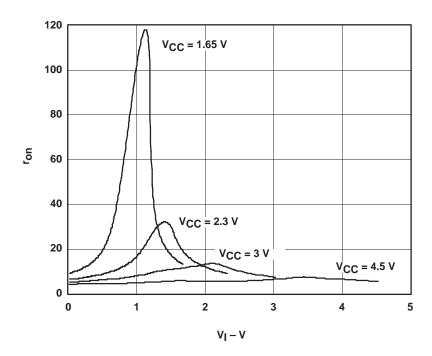
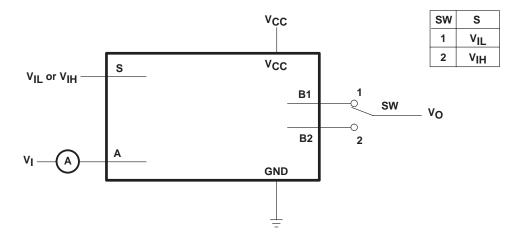


Figure 2. Typical  $r_{on}$  as a Function of Input Voltage (V<sub>I</sub>) for V<sub>I</sub> = 0 to V<sub>CC</sub>



Condition 1:  $V_I = GND$ ,  $V_O = V_{CC}$ Condition 2:  $V_I = V_{CC}$ ,  $V_O = GND$ 

Figure 3. Off-State Switch Leakage-Current Test Circuit

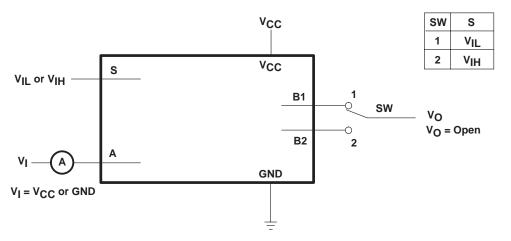
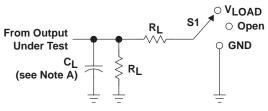


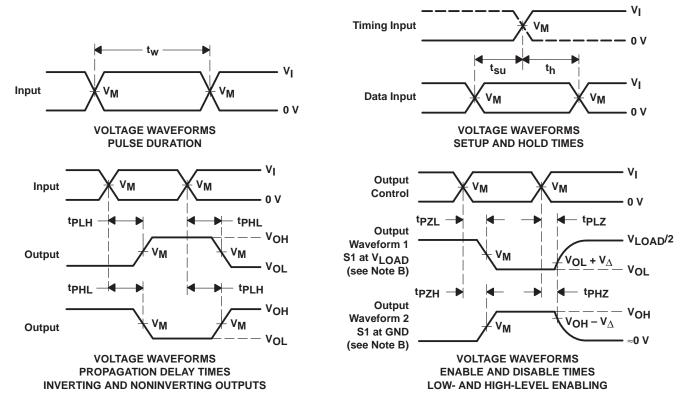
Figure 4. On-State Switch Leakage-Current Test Circuit



TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	VLOAD
tPHZ/tPZH	GND

	CIR	

.,	INPUTS		.,			_	.,
VCC	٧ <sub>I</sub>	t <sub>r</sub> /t <sub>f</sub>	VM	VLOAD	CL	RL	$v_{\scriptscriptstyle\Delta}$
1.8 V $\pm$ 0.15 V	VCC	≤2 ns	V <sub>CC</sub> /2	2×V <sub>CC</sub>	50 pF	500 Ω	0.3 V
2.5 V $\pm$ 0.2 V	VCC	≤ <b>2</b> ns	V <sub>CC</sub> /2	2×VCC	50 pF	500 Ω	0.3 V
3.3 V $\pm$ 0.3 V	VCC	≤2.5 ns	V <sub>CC</sub> /2	2×VCC	50 pF	500 Ω	0.3 V
5 V $\pm$ 0.5 V	VCC	≤2.5 ns	V <sub>CC</sub> /2	2×V <sub>CC</sub>	50 pF	500 Ω	0.3 V



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z<sub>O</sub> = 50 Ω.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.
- H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms



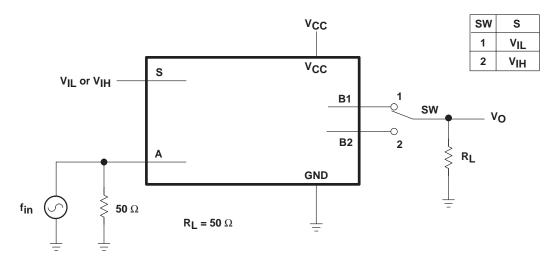


Figure 6. Frequency Response (Switch On)

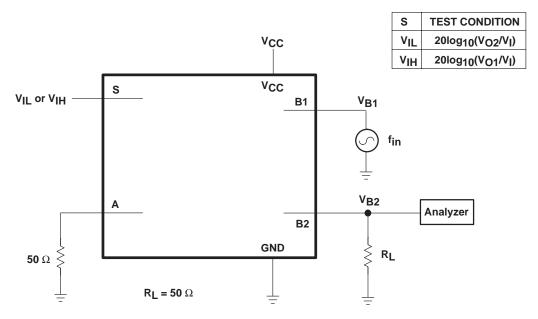


Figure 7. Crosstalk (Between Switches)

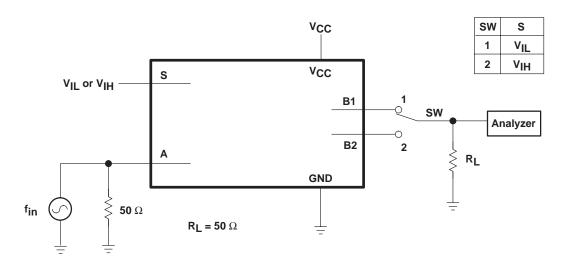


Figure 8. Feed Through

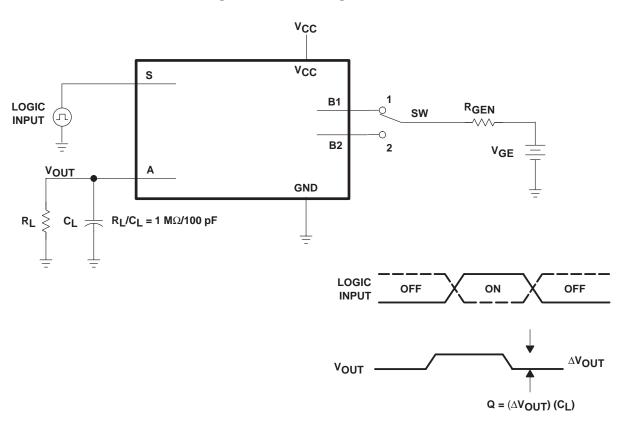


Figure 9. Charge-Injection Test



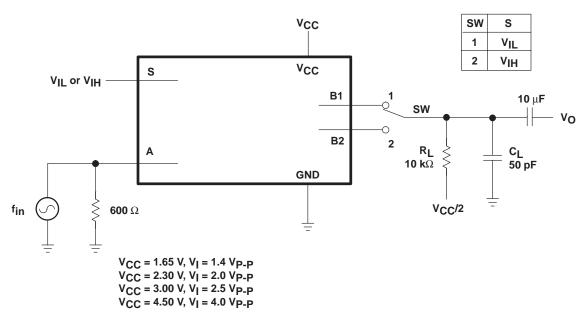


Figure 10. Total Harmonic Distortion

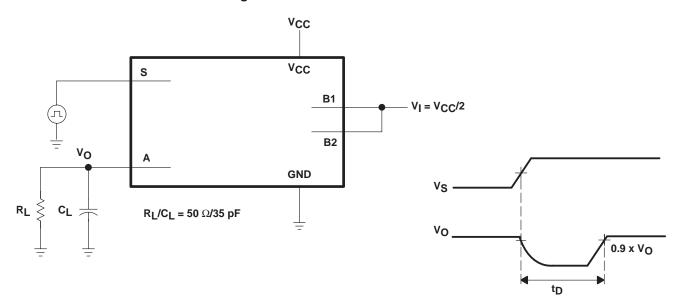
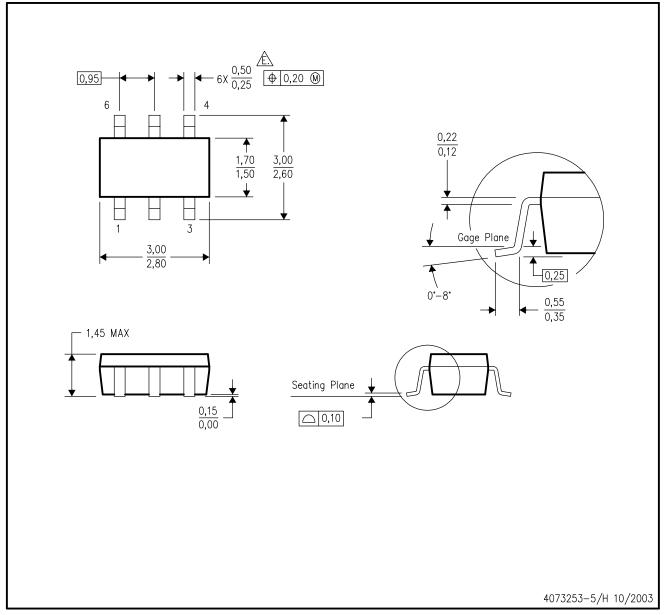


Figure 11. Break-Before-Make Internal Timing

# DBV (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE PACKAGE



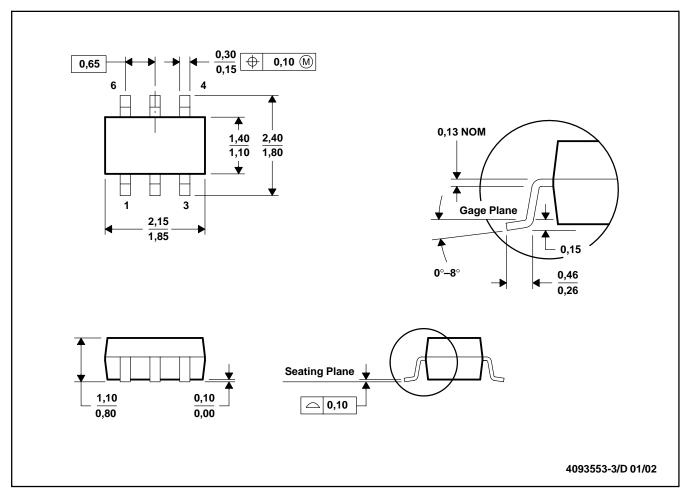
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



# DCK (R-PDSO-G6)

### PLASTIC SMALL-OUTLINE PACKAGE

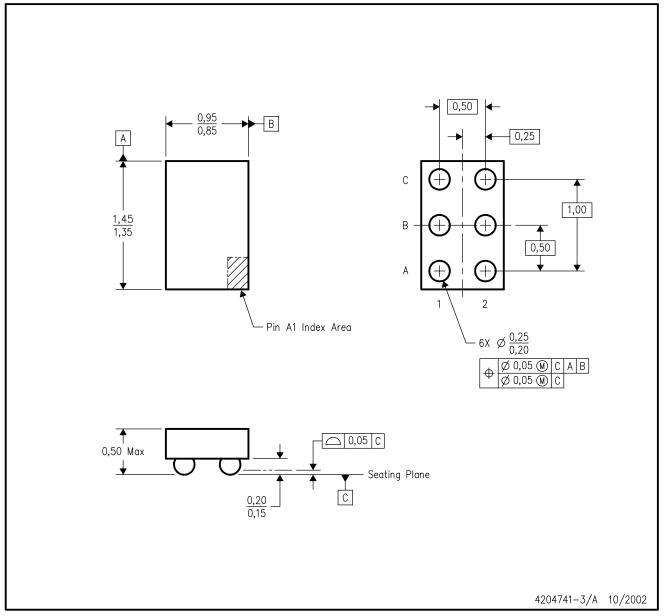


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-203

# YZP (R-XBGA-N6)

# DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

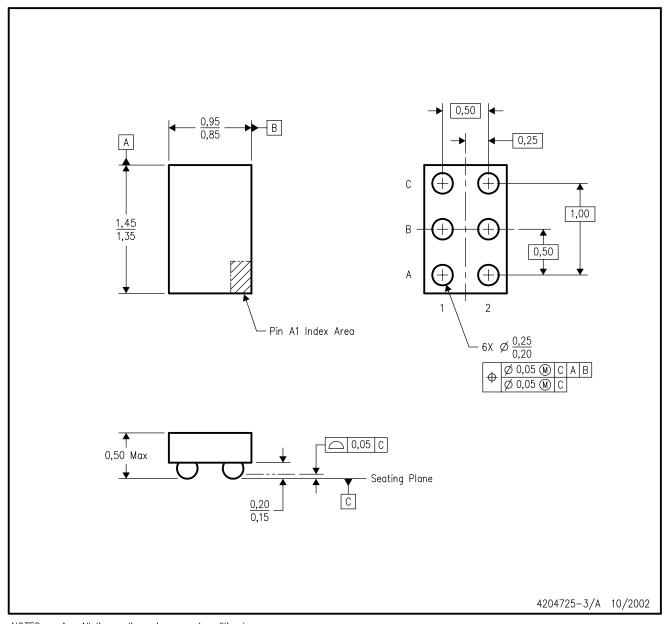
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. This package is lead-free. Refer to the 6 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



# YEP (R-XBGA-N6)

# DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar  $\mathbf{M}$  package configuration.
- D. This package is tin-lead (SnPb). Refer to the 6 YZP package (drawing 4204741) for lead-free.

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